Small Signal Discretes



Never stop thinking

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BGF119

Revision History: 2008-11-18, V3.0

Previous Version: 2008-10-20, V2.0

Page	Subjects (major changes since last revision)
6	Updated Figure 3
All	Target status removed



Transient Voltage Suppressor

Features

- 1 channel TVS diode designed for portable application
- ESD protection according to IEC61000-4-2 for +/-15 kV contact discharge on all IOs
- · Wafer Level Package with SnAgCu solder balls
- RoHS and WEEE compliant package
- Very small form factor

TVS

- High peak pulse power
- Stand-off voltage up to 8 V
- Low clamping voltage factor Vcl/Vbr
- Fast response time



Description

The BGF119 is a single line TVS diode designed for transient voltage and power overstress suppression. All pins are protected against ESD pulses of 15kV contact discharge according to IEC61000-4-2. The wafer level package is a green package with a size of only 0.75 mm x 0.75 mm and a total height of 0.60 mm.

Туре	Package	Marking	Chip
BGF119	WLP-4-1	BGF119	N0742



WLP-4-1-3D



BGF119

Table 1Maximum Ratings

Parameter	Symbol	Values			Unit	Note /
		Min.	Тур.	Max.		Test Condition
Voltage at all pins to GND	V _P	0		8	V	
Operating temperature range	T _{OP}	-30		+85	°C	
Storage temperature range	T _{STG}	-55		+150	°C	
Electrostatic discharge according to IEC61000- $4-2^{1}$ at all pins	V _{ESD}	-15		15	kV	

1) Contact discharge

Table 2Electrical Characteristics¹⁾

Parameter	Symbol	Values			Unit	Note /
		Min.	Тур.	Max.		Test Condition
Line capacitance to GND	CT		230		pF	V _R = 0 V
Forward voltage	$V_{F}^{(2)}$			1.1	V	I _F = 850 mA
Break down voltage	V _{BR}	10	10 11 12	12	V	$I_{\rm R}$ = 15 mA $T_{\rm A}$ = -30°C $T_{\rm A}$ = 25°C $T_{\rm A}$ = 85°C
Clamping voltage during transient	V _{CL} ³⁾			13	V	<i>I</i> _R = 1 A
Leakage current of line to GND	I _R		1 10 100	800	nA	$V_{\rm R} = 8 V$ $T_{\rm A} = -30^{\circ} C$ $T_{\rm A} = 25^{\circ} C$ $T_{\rm A} = 85^{\circ} C$

1) Otherwise specified at $T_A = 25 \text{ °C}$

2) To avoid high temperature and possible disassembling of component from the board, DC current operation to be limited to few seconds

3) 8/20 μs pulse waveform according to IEC61000-4-5

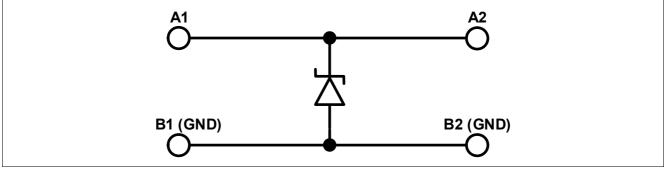
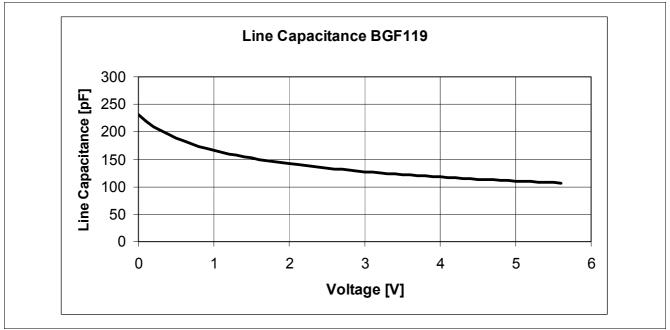
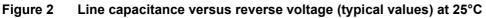
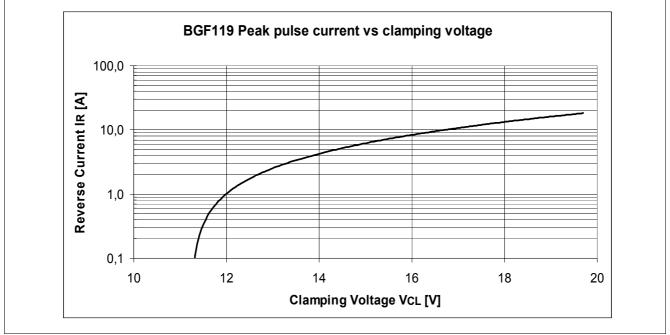


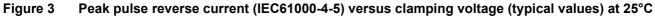
Figure 1 Schematic





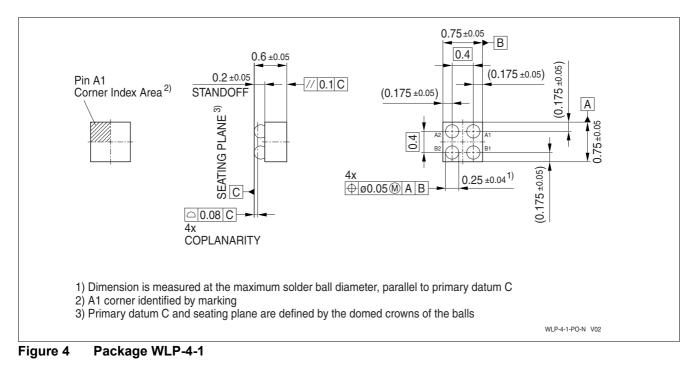








Package Outline



Tape and reel specification

